# **5 V ECL 2-Input AND/NAND**

## MC10EL04, MC100EL04

### Description

The MC10EL/100EL04 is a 2-input AND/NAND gate. The device is functionally equivalent to the E104 device with higher performance capabilities. With propagation delays and output transition times significantly faster than the E104, the EL04 is ideally suited for those applications which require the ultimate in AC performance.

The 100 Series contains temperature compensation.

### Features

- 240 ps Propagation Delay
- ESD Protection:
  - ♦ > 1 kV Human Body Model
  - ♦ > 100 V Machine Model
- PECL Mode Operating Range:  $V_{CC} = 4.2 \text{ V to } 5.7 \text{ V}$ with  $V_{EE} = 0 \text{ V}$
- NECL Mode Operating Range:  $V_{CC} = 0 V$ with  $V_{EE} = -4.2 V$  to -5.7 V
- Internal Input Pulldown Resistors
- Meets or Exceeds JEDEC Spec EIA/JESD78 IC Latchup Test
- Moisture Sensitivity:
  - ◆ Level 1 for SOIC-8 NB
  - ◆ For Additional Information, see Application Note <u>AND8003/D</u>
- Flammability Rating: UL 94 V-0 @ 0.125, Oxygen Index 28 to 34
- Transistor Count = 45 Devices
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



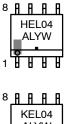
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SOIC-8 NB D SUFFIX CASE 751-07

### MARKING DIAGRAMS\*





#### SOIC-8 NB

H = MC10	Y = Year
K = MC100	W = Work Week
A = Assembly Location	<ul> <li>= Pb–Free Package</li> </ul>
L = Wafer Lot	

(Note: Microdot may be in either location) \*For additional marking information, refer to Application Note <u>AND8002/D</u>.

### **ORDERING INFORMATION**

Device	Package	Shipping
MC10EL04DG	SOIC-8 NB (Pb-Free)	98 Units/Tube
MC100EL04DG	SOIC-8 NB (Pb-Free)	98 Units/Tube

### MC10EL04, MC100EL04

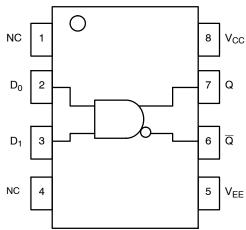


Figure 1. Logic Diagram and Pinout

#### **Table 1. PIN DESCRIPTION**

PIN	FUNCTION
D0, D1	ECL Data Inputs
Q, <u>Q</u>	ECL Data Outputs
V <sub>CC</sub>	Positive Supply
V <sub>EE</sub>	Negative Supply
NC	No Connect

#### **Table 2. MAXIMUM RATINGS**

Symbol	Parameter	Condition 1	Condition 2	Rating	Units
V <sub>CC</sub>	PECL Mode Power Supply	V <sub>EE</sub> = 0 V		8	V
$V_{EE}$	NECL Mode Power Supply	V <sub>CC</sub> = 0 V		-8	V
VI	PECL Mode Input Voltage NECL Mode Input Voltage	V <sub>EE</sub> = 0 V V <sub>CC</sub> = 0 V	$\begin{array}{l} V_I \leq V_{CC} \\ V_I \geq V_{EE} \end{array}$	6 -6	V
l <sub>out</sub>	Output Current	Continuous Surge		50 100	mA
T <sub>A</sub>	Operating Temperature Range			-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
$\theta_{JA}$	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB SOIC-8 NB	190 130	°C/W
$\theta_{\text{JC}}$	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
T <sub>sol</sub>	Wave Solder (Pb-Free)	< 2 to 3 sec @ 260°C		265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### Table 3. 10EL SERIES PECL DC CHARACTERISTICS ( $V_{CC}$ = 5.0 V; $V_{EE}$ = 0.0 V (Note 1))

			–40°C 25°C		85°C						
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I <sub>EE</sub>	Power Supply Current		14	17		14	17		14	17	mA
V <sub>OH</sub>	Output HIGH Voltage (Note 2)	3920	4010	4110	4020	4105	4190	4090	4185	4280	mV
V <sub>OL</sub>	Output LOW Voltage (Note 2)	3050	3200	3350	3050	3210	3370	3050	3227	3405	mV
V <sub>IH</sub>	Input HIGH Voltage	3770		4110	3870		4190	3940		4280	mV
V <sub>IL</sub>	Input LOW Voltage	3050		3500	3050		3520	3050		3555	mV
I <sub>IH</sub>	Input HIGH Current D0 D1			250 150			250 150			250 150	μΑ
IIL	Input LOW Current	0.5			0.5			0.3			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V<sub>CC</sub>. V<sub>EE</sub> can vary +0.25 V / -0.5 V for +25°C and +85°C or V<sub>EE</sub> can vary +0.06 V / -0.5 V for -40°C. 2. Outputs are terminated through a 50  $\Omega$  resistor to V<sub>CC</sub> - 2.0 V.

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### Table 4. 10EL SERIES NECL DC CHARACTERISTICS (V<sub>CC</sub> = 0.0 V; V<sub>EE</sub> = -5.0 V (Note 1))

						•					
			–40°C 25°C		85°C						
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I <sub>EE</sub>	Power Supply Current		14	17		14	17		14	17	mA
V <sub>OH</sub>	Output HIGH Voltage (Note 2)	-1080	-990	-890	-980	-895	-810	-910	-815	-720	mV
V <sub>OL</sub>	Output LOW Voltage (Note 2)	-1950	-1800	-1650	-1950	-1790	-1630	-1950	-1773	-1595	mV
V <sub>IH</sub>	Input HIGH Voltage	-1230		-890	-1130		-810	-1060		-720	mV
V <sub>IL</sub>	Input LOW Voltage	-1950		-1500	-1950		-1480	-1950		-1445	mV
I <sub>IH</sub>	Input HIGH Current D0 D1			250 150			250 150			250 150	μΑ
Ι <sub>ΙL</sub>	Input LOW Current	0.5			0.5			0.3			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

Input and output parameters vary 1:1 with V<sub>CC</sub>. V<sub>EE</sub> can vary +0.25 V / -0.5 V for +25°C and +85°C or V<sub>EE</sub> can vary +0.06 V / -0.5 V for -40°C.
 Outputs are terminated through a 50 Ω resistor to V<sub>CC</sub> - 2.0 V.

#### Table 5. 100EL SERIES PECL DC CHARACTERISTICS (V<sub>CC</sub> = 5.0 V; V<sub>EE</sub> = 0.0 V (Note 1))

			–40°C 25°C		85°C						
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I <sub>EE</sub>	Power Supply Current		14	17		14	17		16	20	mA
V <sub>OH</sub>	Output HIGH Voltage (Note 2)	3915	3995	4120	3975	4045	4120	3975	4050	4120	mV
V <sub>OL</sub>	Output LOW Voltage (Note 2)	3170	3305	3445	3190	3295	3380	3190	3295	3380	mV
V <sub>IH</sub>	Input HIGH Voltage	3835		4120	3835		4120	3835		4120	mV
V <sub>IL</sub>	Input LOW Voltage	3190		3525	3190		3525	3190		3525	mV
IIH	Input HIGH Current D0 D1			250 150			250 150			250 150	μΑ
Ι <sub>ΙL</sub>	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V\_{CC}. V\_{EE} can vary +0.8 V / –0.5 V.

2. Outputs are terminated through a 50  $\Omega$  resistor to  $V_{CC}$  – 2.0 V.

#### Table 6. 100EL SERIES NECL DC CHARACTERISTICS ( $V_{CC} = 0.0 \text{ V}$ ; $V_{EE} = -5.0 \text{ V}$ (Note 1))

			–40°C 25°C			85°C					
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I <sub>EE</sub>	Power Supply Current		14	17		14	17		16	20	mA
V <sub>OH</sub>	Output HIGH Voltage (Note 2)	-1085	-1005	-880	-1025	-955	-880	-1025	-955	-880	mV
V <sub>OL</sub>	Output LOW Voltage (Note 2)	-1830	-1695	-1555	-1810	-1705	-1620	-1810	-1705	-1620	mV
VIH	Input HIGH Voltage	-1165		-880	-1165		-880	-1165		-880	mV
V <sub>IL</sub>	Input LOW Voltage	-1810		-1475	-1810		-1475	-1810		-1475	mV
IIH	Input HIGH Current D0 D1			250 150			250 150			250 150	μΑ
۱ <sub>IL</sub>	Input LOW Current	0.5			0.5			0.5			μA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. Input and output parameters vary 1:1 with V<sub>CC</sub>. V<sub>EE</sub> can vary +0.8 V / –0.5 V.

2. Outputs are terminated through a 50  $\Omega$  resistor to V\_CC – 2.0 V.

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Table 7. AC CHARACTERISTICS	<b>S</b> (V <sub>CC</sub> = 5.0 V; V <sub>EE</sub> = 0.0 V	V or V <sub>CC</sub> = 0.0 V; V <sub>EE</sub> = -5.0 V (Note 1))
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		-40°C		25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f <sub>max</sub>	Maximum Toggle Frequency		TBD			TBD			TBD		GHz
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay to Output	70	235	410	130	240	370	155	265	395	ps
t <sub>JITTER</sub>	Cycle-to-Cycle Jitter		TBD			TBD			TBD		ps
t <sub>r</sub> t <sub>f</sub>	Output Rise/Fall Times Q (20%-80%)	100	225	350	100	225	350	100	225	350	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.

1. 10 Series: V<sub>EE</sub> can vary +0.25 V / -0.5 V for +25°C and +85°C. or V<sub>EE</sub> can vary +0.06 V / -0.5 V for -40°C. 100 Series: V<sub>EE</sub> can vary +0.8 V / -0.5 V.

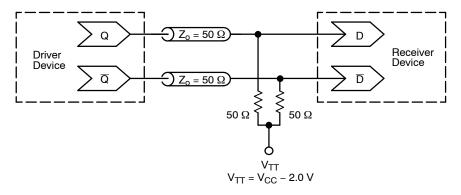


Figure 2. Typical Termination for Output Driver and Device Evaluation (See Application Note <u>AND8020/D</u> – Termination of ECL Logic Devices)

#### **Resource Reference of Application Notes**

- AN1405/D ECL Clock Distribution Techniques
- AN1406/D Designing with PECL (ECL at +5.0 V)
- AN1503/D ECLinPS™ I/O SPiCE Modeling Kit
- AN1504/D Metastability and the ECLinPS Family
- AN1568/D Interfacing Between LVDS and ECL
- AN1672/D The ECL Translator Guide
- AND8001/D Odd Number Counters Design
- AND8002/D Marking and Date Codes
- AND8020/D Termination of ECL Logic Devices
- AND8066/D Interfacing with ECLinPS
- AND8090/D AC Characteristics of ECL Devices

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\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. 4. DRAIN, #2 GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 DRAIN 1 7. 8. **MIRROR 1** STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. LINE 1 OUT 8. STYLE 27: PIN 1. ILIMIT 2 OVI 0 UVLO З. 4. INPUT+ 5. SOURCE SOURCE 6. SOURCE 7. 8 DRAIN

#### DATE 16 FEB 2011

STYLE 4: ANODE ANODE PIN 1. 2. ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 BASE #2 3. COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. 4. GATE 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE 2. EMITTER 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW\_TO\_GND 2. DASIC OFF DASIC\_SW\_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

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SOURCE 1/DRAIN 2

7.

8. GATE 1

7.

8

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COLLECTOR, #1

COLLECTOR, #1

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